









	<p>JANTX2N6796</p>
	<p>codice articolo del costruttore: JANTX2N6796</p> <hr/> <p>Costruttore / Marca: Microsemi</p> <hr/> <p>Parte della descrizione: MOSFET N-CH 100V 8A</p> <hr/> <p>Schede tecniche:  JANTX2N6796.pdf</p> <hr/> <p>Stato di RoHS: Contiene piombo / RoHS non conforme</p> <hr/> <p>Condizione di scorta: New original, 8318 pcs Stock Available.</p> <hr/> <p>Nave da: Hong Kong</p> <hr/> <p>Modo di spedizione: DHL/Fedex/TNT/UPS/EMS</p>
 <p>Not Actual Photo YIC International Co., Limited.</p>	
<p>Image may be representation. See specs for product details.</p>	

specificazioni



















































Numero di parte	JANTX2N6796
fabbricante	Microsemi
Descrizione	MOSFET N-CH 100V 8A
Categoria	Prodotti a semiconduttore discreti > Transistor-FET,
Stato parte	8318 pcs Stock
Serie	Military, MIL-PRF-19500/557
Tecnologia	MOSFET (Metal Oxide)
temperatura di esercizio	-55°C ~ 150°C (TJ)
Tipo montaggio	Through Hole
Contenitore / involucro	TO-205AD, TO-39-3 Metal Can
Contenitore dispositivo fornitore	TO-205AF (TO-39)
Dissipazione di potenza (max)	800mW (Ta), 25W (Tc)
Tipo FET	N-Channel
Caratteristica FET	-
Tensione drain-source (Vdss)	100V
Corrente - Drain continuo (Id) @ 25 ° C	8A (Tc)
Rds On (max) a Id, Vgs	195 mOhm @ 8A, 10V
Vgs (th) (max) a Id	4V @ 250µA
Carica Gate (Qg) (Max) @ Vgs	28.51nC @ 10V
Capacità di ingresso (Ciss) (Max) @ Vds	-
imballaggio	Bulk

Potresti essere anche interessato:

 <p>JANTX2N6798U Microsemi MOSFET N-CH</p>	 <p>JANTX2N6788CDBN SILICONIX JANTX2N6788CDBN SILICONIX</p>	 <p>JANTX2N6794 IR JANTX2N6794 IR</p>	 <p>JANTX2N6800U Microsemi MOSFET N-CH</p>
 <p>JANTX2N6790 Microsemi MOSFET N-CH TO-205AF TO-39</p>	 <p>JANTX2N6798 Microsemi MOSFET N-CH</p>	 <p>JANTX2N6790U Microsemi MOSFET N-CH 18-LCC</p>	 <p>JANTX2N6800 Microsemi MOSFET N-CH</p>

Hot Parts

[Di Più](#)

 120NQ045	 AIC1642-45CX	 AP7362-SP-13	 C1005X8R1H222K050BA	 ES-2R15W S
 FQPF7N10	 ICS9LPR363DGLF	 IRKL41/04AS90	 JAN1N3005B	 JAN1N4622-1
 JAN1N5614	 JAN1N5816	 JAN1N5816	 JAN1N5816R	 JAN1N645DAS
 JAN2N3716	 JAN2N3792	 JANS1N5806US	 JANS2N2222A	 JANTX1N4148UR-1
 JANTX1N4148UR-1	 JANTX1N4148UR-1	 JANTX1N4371AUR-1	 JAN1N4371AUR-1	 JANTX1N4371AUR-1
 JANTX1N4554B	 JANTX1N5807US	 JAN1N6306R	 JANTX1N6638	 JAN1N6638
 JANTX1N914	 JAN1N914	 JANTX1N967B-1	 JANTX2N2369A	 JANTX2N2484UB
 JANTX2N3634	 JANTX2N918	 JANTXM19500/483-01	 JANTXM19500/483-02	 JANTXM19500/483-03
 JANTXV1N1190	 LM158H/883	 LM317LD13TR	 MAX776ESA+T	 MBRP600100CT
 MG25Q2YS9/91	 SN75C3232DWR	 V375A12H600BL	 VE-2N3-MX	 ZTW30512

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